VARIABLE FREQUENCY CONTROL OF THE RESONANT HALF BRIDGE DUAL CONVERTER

Quan Li and Peter Wolfs
Central Queensland University

Abstract

The resonant half bridge dual converter has been previously developed for the DC-DC conversion application in a two-stage photovoltaic Module Integrated Converter (MIC). In order to apply Maximum Power Point Tracking (MPPT) for the PV module or provide variable output voltage, the DC-DC converter is required to operate with variable input/output voltage ratios. This paper studies the variable frequency control of the resonant half bridge dual converter, which is able to produce an output voltage range of 1:2.3 while maintaining resonant switching transitions. The design method of the converter is analysed in detail and the explicit control functions for a 200 W converter are established. Both of the theoretical and simulation waveforms are provided. A resonant half bridge dual converter with the voltage clamp is also proposed at the end of this paper.

1. INTRODUCTION

Figure 1 shows the topology for the resonant half bridge dual converter, which is suitable for the DC-DC conversion stage in the photovoltaic (PV) Module Integrated Converter (MIC). It has achieved reasonable efficiency under high switching frequency by operating the converter under Zero-Voltage Switching (ZVS), [1].

![Figure 1. Resonant Half Bridge Dual Converter](image)

In order to apply Maximum Power Point Tracking (MPPT) to the PV module, the resonant half bridge dual converter is required to produce different input/output voltage ratios. The variable frequency control technique can be applied to the Quasi-Resonant Converters (QRC) under different load conditions to maintain the resonant conditions, [2]. Therefore, the same control can be used to achieve variable converter output voltages under the same input voltage for the resonant half bridge dual converter.

This paper studies the variable frequency operation of the resonant half bridge dual converter, which has an input from the photovoltaic source of 20 V, a maximum output of 340 V and 200 W. A full set of design equations are provided and explicit control functions are obtained through the MATLAB program. Both of the theoretical and simulation waveforms at selected points of operation are given and they agree well with each other. A variation of the basic topology with the additional voltage clamp, which has a low switch voltage stress, is also presented at the end of the paper.

2. VARIABLE FREQUENCY OPERATION

The resonance of the converter can be analysed using the equivalent circuit shown in Figure 2. \( L_r \) is the effective resonant inductor and \( C_1 \) and \( C_2 \) are effective resonant capacitors, where \( C_1 = C_2 = C \). \( D_{Q1} \) and \( D_{Q2} \) are embedded reverse body diodes of the mosfets. The current sources \( I_0 \) model \( L_1 \) and \( L_2 \). Voltage source \( V_d \) is the output capacitor voltage reflected to the primary side and Diode D corresponds to the diodes in the output full bridge rectifier. \( V_d \) and D reverse if the direction of \( i_{L_r} \) reverses.

![Figure 2. Equivalent Circuit](image)

Before \( Q_1 \) turns off, both of \( Q_1 \) and \( Q_2 \) are closed. Figure 3 shows the four possible states after \( Q_1 \) turns off. Equations for the capacitor voltage \( v_{C1} \) and the inductor current \( i_{L_r} \) in each state are listed in Table 1, where \( \sigma_0 = \sqrt{L_r/C} \) is the angular resonance frequency of the resonant tank. The converter has several operational modes that lead to different average values of the absolute resonant inductor current, which controls the rectifier average current on the secondary side and determines the output power of the converter. A continuous inductor current mode is shown in Figure 13. At \( t = 0 \), \( Q_1 \) turns off, the converter moves through three states before \( Q_2 \) turns off. The initial conditions for State (a) are...
The resonant converter has two operation regions: Region 1 where \( \Delta_1 = 0 \) and \( \alpha_d \geq 0 \) and Region 2 where \( \Delta_1 > 0 \). It is required that in both regions \( k \geq 1 \) to maintain ZVS conditions. The discussion can be started in Region 2. In order to determine the converter parameters the timing factor \( \Delta_1 \) and the load factor \( k \) must be given initially. The design equations are:

\[
E \cdot 2I_o = V_o^2 / R
\]  

(1)

\[
V_d \cdot \hat{g}_\Delta(\Delta_1,k) \cdot I_o = V_o^2 / R
\]  

(2)

\[
I_o \cdot Z_0 = k \cdot V_d
\]  

(3)

\[
V_o = N \cdot V_d
\]  

(4)

where \( E \) is the input source voltage, \( V_o \) is the output load voltage and \( R \) is the load resistance. Function \( \hat{g}_\Delta(\Delta_1,k) \) is the ratio of the average of the absolute current in the transformer primary, to the input inductor current, \( I_o \) and is determined by two independent variables, \( \Delta_1 \) and \( k \). From Equations (1) to (4), if \( E, V_o, R \) are also known, \( I_o, V_o, Z_0 \) and \( N \) can be solved. Once the switching frequency is selected, \( L_r \) and \( C \) can be easily obtained.

3.2 Control functions

After \( L_r, C \) and \( N \) are fixed, the load factor \( k \) is no longer an independent variable affecting \( V_o \) or \( V_d \). Then Equation (2) should be rewritten by replacing \( g_\Delta(\Delta_1,k) \) with \( g_\Delta(\Delta_1) \):

\[
V_d \cdot g_\Delta(\Delta_1) \cdot I_o = V_o^2 / R
\]  

(5)

Dividing Equation (5) by (1) yields

\[
V_d = 2E / g_\Delta(\Delta_1)
\]  

(6)

Equation (6) is the control function for the resonant half bridge dual converter. Unfortunately, function \( g_\Delta(\Delta_1) \) cannot be solved directly. An indirect method is to maintain the load factor \( k \) as a variable initially in Equation (6) as

\[
V_d = 2E / \hat{g}_\Delta(\Delta_1,k)
\]  

(7)

and then to eliminate it by applying the circuit constraint obtained through Equations (1) to (4):

\[
k = \frac{N^2 Z_0}{R} \cdot \frac{1}{\hat{g}_\Delta(\Delta_1,k)}
\]  

(8)

Function \( \hat{g}_\Delta(\Delta_1,k) \) can be solved numerically by MATLAB program against a range of \( \Delta_1 \) and \( k \) values and the qualified sets of \( \Delta_1 \) and \( k \) values can be picked by the intersection curve of the surface \( h_{\Delta_1}(\Delta_1,k) = k \).
and the surface \( h_{2,\Delta} (\Delta_1, k) = \frac{N^2 Z_0}{R} \frac{1}{\bar{g}_\Delta (\Delta_1, k)} \). The inherent relationship of \( \Delta_1 \) and \( k \) is then established numerically and substituted back to Equation (7) to derive the control function given in Equation (6) in the form of \( V_d = M_\Delta (\Delta_1) \) by polynomial fitting.

In Region 1, the analysis of the design method and the control algorithm is similar. All Region 1 equations’ counterparts in Region 2 share the same format however the variable \( \Delta_1 \) needs to be replaced by \( \alpha_d \) and the subscript \( \Delta \) by \( \alpha \) to maintain the nomenclatural consistency.

### 3.3 Design process

As a higher output voltage appears in Region 1, the maximum output voltage, 340 V, must be designed in Region 1 with a non-zero delay angle \( \alpha_d \). Other parameters used in the converter design are \( E = 20V \) and \( R = 576\Omega \). According to the counterpart of Equation (7), the surface \( V_d \) in Region 1 can be drawn against \( \alpha_d \) and \( k \) in Figure 4, where \( 0 \leq \alpha_d \leq 10 \text{ radians} \) and \( 1 \leq k \leq 10 \).

![Figure 4. Surface \( V_d \) in Region 1](image)

Before selecting the design parameters, special attention must be paid to the peak mosfet voltage and a reasonable voltage level of 200 V is allowed in the design. From Equations (3) and (13), the peak mosfet voltage can be calculated as

\[
V_{Q,\text{peak}} = \left[ 1 + \sqrt{k^2 + \left( \frac{v_{C1}(t_2)}{V_d} - 1 \right)^2} \right] \cdot V_d \quad (17)
\]

From Equations (9) and (11), \( v_{C1}(t_2) = V_d \) as \( \Delta_1 = 0 \) in Region 1 and Equation (17) can be simplified as

\[
V_{Q,\text{peak}} = (1 + k) \cdot V_d \quad (18)
\]

Then the surface \( V_{Q,\text{peak}} \) can be drawn with a horizontal surface \( V_{Q,\text{rating}} = 200 \text{ V} \) in Figure 5 and an initial set of design parameters is selected where \( \alpha_d = 4 \text{ radians} \) and \( k = 2.3 \), which limits the peak mosfet voltage to 200 V. The following design process shows that other initial sets of \( \alpha_d \) and \( k \) values, whose corresponding points fall on the surface \( V_{Q,\text{peak}} \) and below the surface \( V_{Q,\text{rating}} \), result in similar or smaller ratios of the maximum to minimum output voltage.

![Figure 5. Surfaces \( V_{Q,\text{peak}} \) and \( V_{Q,\text{rating}} \)](image)

The set of the design equations can be solved and the results are given in Table 2. The resonant inductance and capacitance are not listed here because the switching frequency is not selected. The calculations of these parameters will be conducted later when the range of the switching periods is known.

The circuit constraint or the counterpart of Equation (8) is now applied and the surfaces \( h_{1,\alpha} (\alpha_d, k) = k \) and \( h_{2,\alpha} (\alpha_d, k) = \frac{N^2 Z_0}{R} \frac{1}{\bar{g}_\alpha (\alpha_d, k)} \) are drawn in Figure 6.

![Figure 6. Surfaces \( h_{1,\alpha} (\alpha_d, k) \) and \( h_{2,\alpha} (\alpha_d, k) \)](image)
The intersection curve \( u_d \) can be found in Figure 6 and the relationship between \( \alpha_d \) and \( k \) is back substituted to the control function with the dependent variable given by the counterpart of Equation (7). Through polynomial fitting, the control function \( M_d(\alpha_d) \) can be found as

\[
V_d = M_d(\alpha_d) = 0.0079\alpha_d^3 + 0.2124\alpha_d^2 + 5.4130\alpha_d + 41.7942
\]  \hspace{1cm} (19)

The control function \( M_d(\alpha_d) \) is drawn in Figure 7. When \( \alpha_d \) reaches zero, Region 1 operation ends and Region 2 operation starts. At this point, \( \alpha_d = 0 \), \( k = 1.59 \) and \( V_d = 41.8 \text{ V} \).

The design process in Region 2 is similar and the surface \( V_d \) is drawn against \( \Delta_1 \) and \( k \) in Figure 8, where \( 0 \leq \Delta_1 \leq 3 \) and \( 1 \leq k \leq 10 \). It is worth noting that the peak mosfet voltage in Equation (17) is well below 200 V when \( k \leq 1.59 \). The surfaces

\[ h_{1,1}(\Delta_1,k) = k \quad \text{and} \quad h_{2,1}(\Delta_1,k) = \frac{N^2Z_n}{R} \frac{1}{\hat{g}_A(\Delta_1,k)} \]

in the circuit constraint of Equation (8) are drawn in Figure 9. The intersection curve \( u_d \) can be found and the numerical relationship between \( \Delta_1 \) and \( k \) is back substituted to Equation (7). Through polynomial fitting, the control function \( M_A(\Delta_1) \) can be found as:

\[
v_d = M_A(\Delta_1) = 0.3005\Delta_1^3 + 0.0221\Delta_1^2 - 9.0395\Delta_1 + 41.7931
\]  \hspace{1cm} (20)

The control function \( M_A(\Delta_1) \) can be drawn in Figure 10. When \( \Delta_1 = 2 \), \( k = 1 \) and \( V_d = 26.2 \text{ V} \). A switching frequency of 500 kHz is selected for the lowest output voltage when \( \Delta_1 = 2 \) and \( k = 1 \). The angular resonance frequency of the resonant tank and the switching frequency when \( \alpha_d = 4 \text{ radians} \) and \( k = 2.31 \) are given in Table 3. The resonant components are \( L_r = 6.85 \mu\text{H} \) and \( C = 8.82 \text{ nF} \).

4. THEORECTICAL AND SIMULATION WAVEFORMS

The theoretical waveforms are generated by plotting Equations (9) to (16) at different \( \Delta_1 \) or \( \alpha_d \) and \( k \) values and the simulation is performed with SIMULINK. The selected operating points are listed in Table 4 and their corresponding waveforms are shown in Figures 11 to 16.
Figure 11. Theoretical Waveforms

Figure 12. Theoretical Waveforms

Figure 13. Theoretical Waveforms

Figure 14. Simulation Waveforms

Figure 15. Simulation Waveforms

Figure 16. Simulation Waveforms
Figure 17 shows a variation of the resonant half bridge dual converter, which includes a voltage clamping circuit formed by two coupled inductors and two extra diodes. The analysis of this converter is similar to the converter without the voltage clamp. This topology achieves lower voltage stresses across the main switches. However, high returned energy by the clamp windings of the coupled inductors could be a problem and may significantly lower the converter efficiency if no further measures are taken.

5. CONCLUSIONS

This paper studies the variable frequency control of the resonant half bridge dual converter based on varying the timing factor $\Delta_1$ or the delay angle $\alpha_d$ and the load factor $k$. Under variable frequency control, the resonant half bridge dual converter operates with a variable input/output voltage ratio. With a reasonable switch voltage stress, the resonant converter without the voltage clamp is able to achieve a $146 \text{ V}$ to $340 \text{ V}$ output voltage range. The resonant converter with the voltage clamp has a lower switch voltage stress but a lower efficiency due to the returned energy in the inductor clamp windings.

6. REFERENCES

